

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A method of forming a gate electrode in a semiconductor device, comprising the steps of:
  - forming a gate oxide on a semiconductor substrate;
  - depositing polysilicon on the gate oxide;
  - forming a mask formation film on the polysilicon;
  - patterning the mask formation film twice, using a photolithography process for each patterning, wherein one photolithography process is performed with a mask pattern which masks neighboring gate electrode areas and an area between the neighboring gate electrode areas, and the other photolithography process is performed with a mask pattern which exposes the area between the neighboring gate electrode areas;
  - etching the polysilicon using the patterned mask formation film; and
  - removing the mask formation film remaining on the polysilicon.
2. (Previously Presented) The method of claim 1, wherein the mask formation film is patterned by a photolithography process with a mask pattern which masks neighboring gate electrode areas and the area between the neighboring gate electrode areas, and then by a photolithography process with a mask pattern which exposes the area between the neighboring gate electrode areas.
3. (Currently Amended) The method of claim 1, wherein the mask formation film is patterned by a photolithography process with a mask pattern which exposes the area between the neighboring gate electrode areas, and then by a photolithography process with a mask pattern which masks neighboring gate electrode areas and the area between neighboring gate electrode areas.
4. (Currently Amended) The method of claim 1, wherein the mask ~~thin~~ formation film is made from material having a great ~~difference~~ difference in etching rate from the polysilicon.

5. (Currently Amended) The method of claim 4, wherein the mask ~~thin~~ formation film is silicon oxynitride or silicon nitride.

6. (Currently Amended) A method of forming a gate electrode in a semiconductor device, comprising the steps of:

forming a gate oxide on a silicon substrate;

depositing a polysilicon to function as a gate electrode on the gate oxide, and then forming a mask formation film to be used as a mask when the gate electrode is etched from the polysilicon;

forming a first pattern of photoresist on the mask formation film, and then performing a first etching step of etching the mask formation film based on the first pattern of photoresist;

removing the first pattern of photoresist;

forming a second pattern of photoresist on a portion of the mask formation film remaining after the first etching step and on the polysilicon, and then performing a second etching step of etching the mask formation film based on the second pattern of photoresist;

removing the second pattern of photoresist, and then etching the polysilicon using the mask ~~thin~~ formation film partially remaining on the polysilicon; and

forming the gate electrode by removing the mask formation film remaining on the polysilicon.

7. (Previously Presented) The method of claim 6, wherein the mask formation film is made from material having a great difference in etching rate from the polysilicon.

8. (Previously Presented) The method of claim 1 or 7, wherein the mask formation film is silicon oxynitride or silicon nitride deposited by a PECVD method.

9. (Previously Presented) The method of claim 6, wherein the etching of the mask formation film in the first and second etching steps is performed until the polysilicon is exposed.

10. (Previously Presented) The method of claim 6, wherein, in the step of forming the gate electrode, the mask formation film is removed by a wet etching.